L Number	Hits	Search Text	DB	Time stamp
1	6802	257/173,328,355-363,546,758.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 18:20
2	1004	438/212,268,309.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 18:21
3	7713	257/173,328,355-363,546,758.ccls. or 438/212,268,309.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 18:21
4	4176	(257/173,328,355-363,546,758.ccls. or 438/212,268,309.ccls.) and (semiconductor near (layer substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:13
5	2887	((257/173,328,355-363,546,758.ccls. or 438/212,268,309.ccls.) and (semiconductor near (layer substrate))) and (source drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:14
6	2154	(((257/173,328,355-363,546,758.ccls. or 438/212,268,309.ccls.) and (semiconductor near (layer substrate))) and (source drain)) and (gate near (insulat$3 oxide electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:14
7	727	((((257/173,328,355-363,546,758.ccls. or 438/212,268,309.ccls.) and (semiconductor near (layer substrate))) and (source drain)) and (gate near (insulat$3 oxide electrode))) and (interlevel$1 interconnect$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:09
8	143	(((((257/173,328,355-363,546,758.ccls. or 438/212,268,309.ccls.) and (semiconductor near (layer substrate))) and (source drain)) and (gate near (insulat$3 oxide electrode))) and (interlevel$1 interconnect$3)) and electrostatic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:10
9	3	("5086365" | "5963409" | "6080612").PN.	USPAT	2004/04/16 18:54
10	9	("4997786" | "5534459" | "5610790" | "5880001" | "5897939" | "5899714" | "5930638" | "5953600" | "5970333").PN.	USPAT	2004/04/16 18:54
11	11	("4609931" | "4616243" | "4692834" | "4745450" | "5124578" | "5272586" | "5287241" | "5440162" | "5479039" | "5498892" | "5663678").PN.	USPAT	2004/04/16 18:56
12	727	((((257/173,328,355-363,546,758.ccls. or 438/212,268,309.ccls.) and (semiconductor near (layer substrate))) and (source drain)) and (gate near (insulat$3 oxide electrode))) and (interlevel$1 interconnect$3 IDL)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:11
13	143	(((((257/173,328,355-363,546,758.ccls. or 438/212,268,309.ccls.) and (semiconductor near (layer substrate))) and (source drain)) and (gate near (insulat$3 oxide electrode))) and (interlevel$1 interconnect$3 IDL)) and electrostatic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:11
14	739	((((257/173,328,355-363,546,758.ccls. or 438/212,268,309.ccls.) and (semiconductor near (layer substrate))) and (source drain)) and (gate near (insulat$3 oxide electrode))) and (interlevel$1 interconnect$3 ILD)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:14

C:\APPS\east\workspaces\default.wsp

15	146	(((((257/173,328,355-363,546,758.ccls. or 438/212,268,309.ccls.) and (semiconductor near (layer substrate))) and (source drain)) and (gate near (insulat$3 oxide electrode))) and (interlevel$1 interconnect$3 ILD)) and electrostatic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:13
16	341067	257/$.ccls. 438/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:13
17	10480	(257/$.ccls. 438/$.ccls.) and electrostatic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:20
18	8796	((257/$.ccls. 438/$.ccls.) and electrostatic) and ((semiconductor near (layer substrate)) substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:20
19	6392	(((257/$.ccls. 438/$.ccls.) and electrostatic) and ((semiconductor near (layer substrate)) substrate)) and (source drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:20
20	3295	((((257/$.ccls. 438/$.ccls.) and electrostatic) and ((semiconductor near (layer substrate)) substrate)) and (source drain)) and (gate near (insulat$3 oxide electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:21
21	1091	(((((257/$.ccls. 438/$.ccls.) and electrostatic) and ((semiconductor near (layer substrate)) substrate)) and (source drain)) and (gate near (insulat$3 oxide electrode))) and (interlevel$1 interconnect$3 ILD)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:18
22	3	((((((257/$.ccls. 438/$.ccls.) and electrostatic) and ((semiconductor near (layer substrate)) substrate)) and (source drain)) and (gate near (insulat$3 oxide electrode))) and (interlevel$1 interconnect$3 ILD)) and ((first near (interlevel ILD)) with (second near (interlevel ILD)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:19
23	1098	(((((257/$.ccls. 438/$.ccls.) and electrostatic) and ((semiconductor near (layer substrate)) substrate)) and (source drain)) and (gate near (insulat$3 oxide electrode))) and (inter$1level$1 interconnect$3 ILD)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:21
24	3	((((((257/$.ccls. 438/$.ccls.) and electrostatic) and ((semiconductor near (layer substrate)) substrate)) and (source drain)) and (gate near (insulat$3 oxide electrode))) and (inter$1level$1 interconnect$3 ILD)) and ((first near (interlevel ILD)) with (second near (interlevel ILD)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:19
25	3	((((((257/$.ccls. 438/$.ccls.) and electrostatic) and ((semiconductor near (layer substrate)) substrate)) and (source drain)) and (gate near (insulat$3 oxide electrode))) and (inter$1level$1 interconnect$3 ILD)) and ((first near (inter$1level ILD)) with (second near (inter$1level ILD)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:22
26	267605	electrostatic ESD	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:20

27	71784	(electrostatic ESD) and ((semiconductor near (layer substrate)) substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:39
28	39347	((electrostatic ESD) and ((semiconductor near (layer substrate)) substrate)) and (source drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:39
29	5862	(((electrostatic ESD) and ((semiconductor near (layer substrate)) substrate)) and (source drain)) and (gate near (insulat$3 oxide electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:39
30	1783	((((electrostatic ESD) and ((semiconductor near (layer substrate)) substrate)) and (source drain)) and (gate near (insulat$3 oxide electrode))) and (inter$1level$1 interconnect$3 ILD)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:28
31	4	(((((electrostatic ESD) and ((semiconductor near (layer substrate)) substrate)) and (source drain)) and (gate near (insulat$3 oxide electrode))) and (inter$1level$1 interconnect$3 ILD)) and ((first near (inter$1level ILD)) with (second near (inter$1level ILD)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:22
32	11	(((((electrostatic ESD) and ((semiconductor near (layer substrate)) substrate)) and (source drain)) and (gate near (insulat$3 oxide electrode))) and (inter$1level$1 interconnect$3 ILD)) and ((first near (inter$1level ILD)) same (second near (inter$1level ILD)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:24
33	0	(first near gate near interconnect$3) with (first near drain near interconnect$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:36
34	0	(first near gate near interconnect$3) same (first near drain near interconnect$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:26
35	2	(first near gate near interconnect$3) and (first near drain near interconnect$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:26
36	253785	((semiconductor near (layer substrate)) substrate) same (source drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:27
37	31265	(((semiconductor near (layer substrate)) substrate) same (source drain)) and ((gate near (insulat$3 oxide)) with (gate near electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:28
38	5854	((((semiconductor near (layer substrate)) substrate) same (source drain)) and ((gate near (insulat$3 oxide)) with (gate near electrode))) and (inter$1level$1 interconnect$3 ILD)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:39

39	186	(gate near interconnect$3) with (drain near interconnect$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:29
40	46	(((((semiconductor near (layer substrate)) substrate) same (source drain)) and ((gate near (insulat$3 oxide)) with (gate near electrode))) and (inter$1level$1 interconnect$3 ILD)) and ((gate near interconnect$3) with (drain near interconnect$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:29
41	0	(first near gate near (contact$3 interconnect$3)) with (first near drain near (contact3 interconnect$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:37
42	197	(gate near (contact$3 interconnect$3)) with (drain near (contact3 interconnect$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:37
43	23	((gate near (contact$3 interconnect$3)) with (drain near (contact3 interconnect$3))) and (electrostatic ESD)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:49
44	158	((gate near (contact$3 interconnect$3)) with (drain near (contact3 interconnect$3))) and ((semiconductor near (layer substrate)) substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:48
45	158	(((gate near (contact$3 interconnect$3)) with (drain near (contact3 interconnect$3))) and ((semiconductor near (layer substrate)) substrate)) and (source drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:48
46	141	((((gate near (contact$3 interconnect$3)) with (drain near (contact3 interconnect$3))) and ((semiconductor near (layer substrate)) substrate)) and (source drain)) and (gate near (insulat$3 oxide electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:48
47	141	(((((gate near (contact$3 interconnect$3)) with (drain near (contact3 interconnect$3))) and ((semiconductor near (layer substrate)) substrate)) and (source drain)) and (gate near (insulat$3 oxide electrode))) and (inter$1level$1 interconnect$3 ILD)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:47
48	398	(first near (inter$1level ILD)) with (second near (inter$1level ILD))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:50
49	374	((first near (inter$1level ILD)) with (second near (inter$1level ILD))) and ((semiconductor near (layer substrate)) substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:48
50	274	(((first near (inter$1level ILD)) with (second near (inter$1level ILD))) and ((semiconductor near (layer substrate)) substrate)) and (source drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:48

C:\APPS\east\workspaces\default.wsp

L Number	Hits	Search Text	DB	Time stamp
51	222	((((first near (inter$1level ILD)) with (second near (inter$1level ILD))) and ((semiconductor near (layer substrate)) substrate)) and (source drain)) and (gate near (insulat$3 oxide electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:49
52	4	(((((first near (inter$1level ILD)) with (second near (inter$1level ILD))) and ((semiconductor near (layer substrate)) substrate)) and (source drain)) and (gate near (insulat$3 oxide electrode))) and (electrostatic ESD)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:49
53	57	(first near (inter$1level ILD)) with (second near (inter$1level ILD)) with (third near (inter$1level ILD))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:57
54	6	((first near (inter$1level ILD)) with (second near (inter$1level ILD))) and ((gate near (interconnect contact wir$3)) with (drain near (interconnect contact wir$3)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 20:12
55	2004	((gate near (interconnect contact wir$3)) with (drain near (interconnect contact wir$3)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 20:13
56	179	(((gate near (interconnect contact wir$3)) with (drain near (interconnect contact wir$3)))) and (electrostatic ESD)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 20:13